1M x 1 Bit Static Random Access Memory

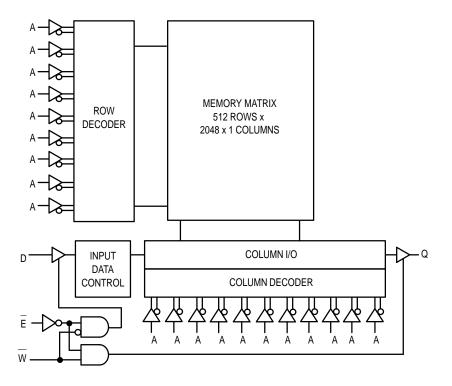
The MCM6227B is a 1,048,576 bit static random–access memory organized as 1,048,576 words of 1 bit. Static design eliminates the need for external clocks or timing strobes while CMOS circuitry reduces power consumption and provides for greater reliability.

The MCM6227B is each equipped with a chip enable (E) pin. This feature provides reduced system power requirements without degrading access time performance

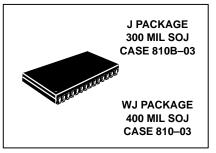
The MCM6227B is available in 300 mil and 400 mil, 28-lead surface-mount SOJ packages.

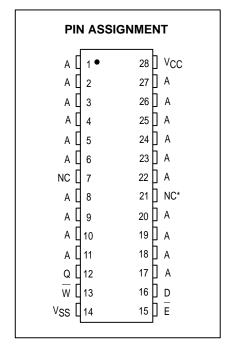
- Single 5 V ± 10% Power Supply
- Fast Access Times: 15/17/20/25/35 ns
- Equal Address and Chip Enable Access Times
- Input and Output are TTL Compatible
- Three-State Output
- Low Power Operation: 115/110/105/100/95 mA Maximum, Active AC

BLOCK DIAGRAM



MCM6227B





PIN NAMES							
A. Address Inputs W Write Enable E Chip Enable D Data Input Q Data Output NC No Connection VCC +5 V Power Supply VSS Ground							

*If not used for no connect, then do not exceed voltages of -0.5 to V_{CC} + 0.5 V. This pin is used for manufacturing diagnostics.

REV 3 10/31/96



TRUTH TABLE

Е	W	Mode	I/O Pin Cycle		Current	
Н	Х	Not Selected	High–Z	1	I _{SB1} , I _{SB2}	
L	Н	Read	D _{out}	Read	ICCA	
L	L	Write	High-Z	Write	ICCA	

H = High, L = Low, X = Don't Care

ABSOLUTE MAXIMUM RATINGS (See Note)

Rating	Symbol	Value	Unit
Power Supply Voltage Relative to V _{SS}	Vcc	- 0.5 to 7.0	V
Voltage Relative to VSS for Any Pin Except VCC	V _{in} , V _{out}	- 0.5 to V _{CC} + 0.5	V
Output Current	l _{out}	± 20	mA
Power Dissipation	PD	1.1	W
Temperature Under Bias	T _{bias}	- 10 to + 85	°C
Operating Temperature	TA	0 to + 70	°C
Storage Temperature	T _{stg}	- 55 to + 150	°C

NOTE: Permanent device damage may occur if ABSOLUTE MAXIMUM RATINGS are exceeded. Functional operation should be restricted to RECOMMENDED OPER-ATING CONDITIONS. Exposure to higher than recommended voltages for extended periods of time could affect device reliability.

This device contains circuitry to protect the inputs against damage due to high static voltages or electric fields; however, it is advised that normal precautions be taken to avoid application of any voltage higher than maximum rated voltages to these high–impedance circuits.

This CMOS memory circuit has been designed to meet the dc and ac specifications shown in the tables, after thermal equilibrium has been established. The circuit is in a test socket or mounted on a printed circuit board and transverse air flow of at least 500 linear feet per minute is maintained.

DC OPERATING CONDITIONS AND CHARACTERISTICS

 $(V_{CC} = 5.0 \text{ V} \pm 10\%, T_A = 0 \text{ to } 70^{\circ}\text{C}, \text{ Unless Otherwise Noted})$

RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	Min	Max	Unit
Supply Voltage (Operating Voltage Range)	Vcc	4.5	5.5	V
Input High Voltage	VIH	2.2	V _{CC} +0.3**	V
Input Low Voltage	V _{IL}	- 0.5*	0.8	V

^{*} V_{IL} (min) = -0.5 V dc; V_{IL} (min) = -2.0 V ac (pulse width ≤ 20 ns).

DC CHARACTERISTICS AND SUPPLY CURRENTS

Parameter		Symbol	Min	Max	Unit
Input Leakage Current (All Inputs, V _{in} = 0 to V _{CC})		l _{lkg(l)}	_	± 1	μΑ
Output Leakage Current (E = V _{IH} , V _{out} = 0 to V _{CC})		l _{lkg(O)}	_	± 1	μΑ
AC Active Supply Current (I _{out} = 0 mA, V _{CC} = max)	MCM6227B-15: t _{AVAV} = 15 ns MCM6227B-17: t _{AVAV} = 17 ns MCM6227B-20: t _{AVAV} = 20 ns MCM6227B-25: t _{AVAV} = 25 ns MCM6227B-35: t _{AVAV} = 35 ns	ICCA		115 110 105 100 95	mA
AC Standby Current ($V_{CC} = max$, $E = V_{IH}$, $f \le f_{max}$)	MCM6227B-15: t _{AVAV} = 15 ns MCM6227B-17: t _{AVAV} = 17 ns MCM6227B-20: t _{AVAV} = 20 ns MCM6227B-25: t _{AVAV} = 25 ns MCM6227B-35: t _{AVAV} = 35 ns	ISB1	- - - -	40 35 30 25 20	mA
CMOS Standby Current (E \geq V _{CC} $-$ 0.2 V, V _{in} \leq V _{SS} + 0. or \geq V _{CC} $-$ 0.2 V, V _{CC} $=$ max, f $=$ 0 MHz)	I _{SB2}	_	5	mA	
Output Low Voltage (I _{OL} = + 8.0 mA)		V _{OL}	_	0.4	٧
Output High Voltage (I _{OH} = - 4.0 mA)		Voн	2.4	_	V

^{**} V_{IH} (max) = V_{CC} + 0.3 V dc; V_{IH} (max) = V_{CC} + 2 V ac (pulse width \leq 20 ns).

CAPACITANCE (f = 1.0 MHz, dV = 3.0 V, $T_A = 25$ °C, Periodically Sampled Rather Than 100% Tested)

	Symbol	Тур	Max	Unit	
Input Capacitance	All Inputs Except Clocks and D, Q E and W	C _{in}	4 5	6 8	pF
Input and Output Capacitance	D, Q	C _{in} , C _{out}	5	8	pF

AC OPERATING CONDITIONS AND CHARACTERISTICS

(V_{CC} = 5.0 V \pm 10%, T_A = 0 to + 70°C, Unless Otherwise Noted)

Input Pulse Levels 0 to 3.0 V	Output Timing Measurement Reference Level 1.5 V
Input Rise/Fall Time	Output Load See Figure 1a
Input Timing Measurement Reference Level 1.5 V	

READ CYCLE TIMING (See Notes 1 and 2)

		6227	B-15	6227	B-17	6227	B-20	6227	B-25	6227	B-35		
Parameter	Symbol	Min	Max	Unit	Notes								
Read Cycle Time	t _{AVAV}	15	_	17	_	20	_	25	_	35	_	ns	2, 3
Address Access Time	^t AVQV	_	15	_	17	_	20	_	25	_	35	ns	
Enable Access Time	^t ELQV	_	15	_	17	_	20	_	25	_	35	ns	4
Output Hold from Address Change	tAXQX	5	_	5	_	5	_	5	_	5	_	ns	
Enable Low to Output Active	tELQX	5	_	5	_	5	_	5	_	5	_	ns	5, 6, 7
Enable High to Output High–Z	^t EHQZ		6	_	7	_	7		8		8	ns	5, 6, 7

NOTES:

- 1. W is high for read cycle.
- 2. Product sensitivities to noise require proper grounding and decoupling of power supplies as well as minimization or elimination of bus contention conditions during read and write cycles.
- 3. All timings are referenced from the last valid address to the first transitioning address.
- 4. Addresses valid prior to or coincident with E going low.
- 5. At any given voltage and temperature, tehoz max is less than telox min, both for a given device and from device to device.
- 6. Transition is measured $\pm\,500$ mV from steady–state voltage with load of Figure 1b.
- 7. This parameter is sampled and not 100% tested.
- 8. Device is continuously selected (E ≤ V_{IL}).

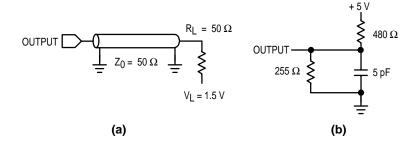


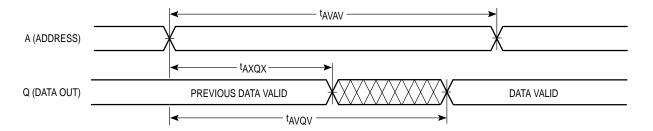
Figure 1. AC Test Loads

TIMING LIMITS

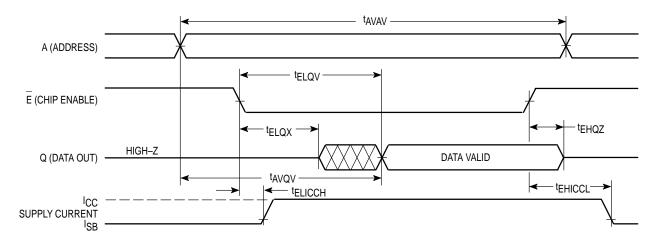
The table of timing values shows either a minimum or a maximum limit for each parameter. Input requirements are specified from the external system point of view. Thus, address setup time is shown as a minimum since the system must supply at least that much time. On the other hand, responses from the memory are specified from the device point of view. Thus, the access time is shown as a maximum since the device never provides data later than that time.

MOTOROLA FAST SRAM MCM6227B

READ CYCLE 1 (See Notes 1, 2, and 8)



READ CYCLE 2 (See Note 4)



MCM6227B MOTOROLA FAST SRAM

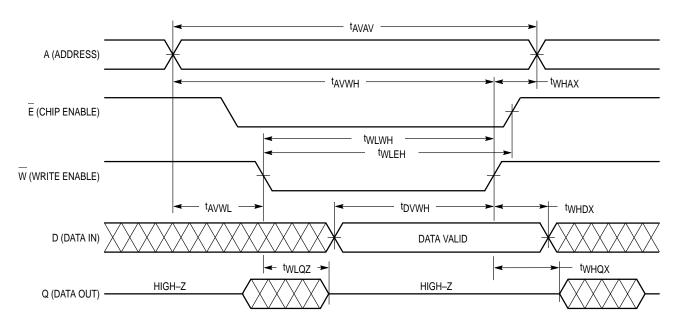
WRITE CYCLE 1 (W Controlled, See Notes 1 and 2)

		6227	B-15	6227	B-17	6227	B-20	6227	B-25	6227	B-35		
Parameter	Symbol	Min	Max	Unit	Notes								
Write Cycle Time	tavav	15	_	17	_	20	_	25	_	35	_	ns	3
Address Setup Time	t _{AVWL}	0	_	0	_	0	_	0	_	0	_	ns	
Address Valid to End of Write	^t AVWH	12	_	14	_	15	_	17	_	20	_	ns	
Write Pulse Width	^t WLWH, ^t WLEH	12	_	14	_	15	_	17	_	20	_	ns	
Data Valid to End of Write	^t DVWH	7	_	8	_	8	_	10	_	11	_	ns	
Data Hold Time	tWHDX	0	_	0	_	0	_	0	_	0	_	ns	
Write Low to Data High-Z	tWLQZ	_	6	_	7	_	7	_	8	_	8	ns	4, 5, 6
Write High to Output Active	tWHQX	5	_	5	_	5	_	5	_	5	_	ns	4, 5, 6
Write Recovery Time	tWHAX	0	_	0	_	0	_	0	_	0	_	ns	

NOTES:

- 1. A write occurs during the overlap of E low and W low.
- 2. Product sensitivities to noise require proper grounding and decoupling of power supplies as well as minimization or elimination of bus contention conditions during read and write cycles.
- 3. All timings are referenced from the last valid address to the first transitioning address.
- 4. Transition is measured \pm 500 mV from steady–state voltage with load of Figure 1b.
- 5. This parameter is sampled and not 100% tested.
- 6. At any given voltage and temperature, t_{WLQZ} max is less than t_{WHQX} min both for a given device and from device to device.

WRITE CYCLE 1 (W Controlled See Notes 1 and 2)



MOTOROLA FAST SRAM MCM6227B

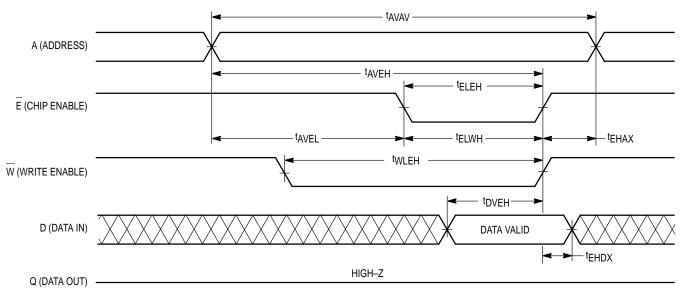
WRITE CYCLE 2 (E Controlled, See Notes 1 and 2)

		6227	B-15	6227	B-17	6227	B-20	6227	B-25	6227	B-35		
Parameter	Symbol	Min	Max	Unit	Notes								
Write Cycle Time	tAVAV	15	_	17	_	20	_	25	_	35	_	ns	3
Address Setup Time	†AVEL	0	_	0	_	0	_	0	_	0	_	ns	
Address Valid to End of Write	^t AVEH	12	_	14	_	15	_	17	_	20	_	ns	
Enable to End of Write	tELEH, tELWH	10	_	11	_	12	_	15	_	20	_	ns	4, 5
Write Pulse Width	tWLEH	12	_	14	_	15	_	17	_	20	_	ns	
Data Valid to End of Write	tDVEH	7	_	8	_	8	_	10	_	11	_	ns	
Data Hold Time	tEHDX	0	_	0	_	0	_	0	_	0	_	ns	
Write Recovery Time	^t EHAX	0	_	0	_	0	_	0	_	0	_	ns	

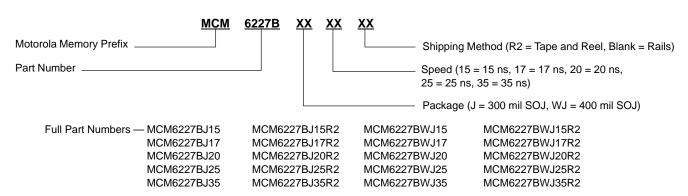
NOTES:

- 1. A write occurs during the overlap of E low and W low.
- 2. Product sensitivities to noise require proper grounding and decoupling of power supplies as well as minimization or elimination of bus contention conditions during read and write cycles.
- 3. All_timings are referenced from the last valid address to the first transitioning address.
- 4. If <u>E</u> goes low coincident with or after W goes low, the output will remain in a high–impedance state.
- 5. If E goes high coincident with or before W goes high, the output will remain in a high–impedance state.

WRITE CYCLE 2 (E Controlled See Notes 1 and 2)

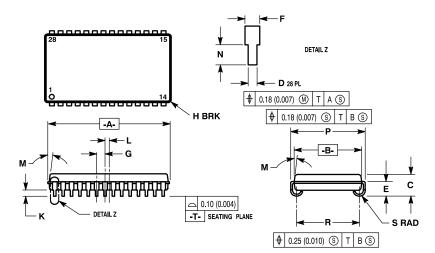


ORDERING INFORMATION (Order by Full Part Number)



PACKAGE DIMENSIONS

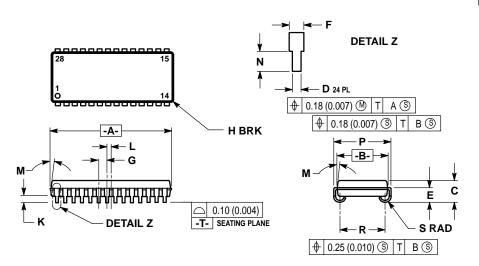
28 LEAD 400 MIL SOJ CASE 810-03



- NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. DIMENSION A & B DO NOT INCLUDE MOLD PROTRUSION MOLD PROTRUSION SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
 3. CONTROLLING DIMENSION: INCH.
- DIM R TO BE DETERMINED AT DATUM -T-.

	MILLIM	ETERS	INCHES				
DIM	MIN	MAX	MIN	MAX			
Α	18.29	18.54	0.720	0.730			
В	10.04	10.28	0.395	0.405			
С	3.26	3.75	0.128	0.148			
D	0.39	0.50	0.015	0.020			
E	2.24	2.48	0.088	0.098			
F	0.67	0.81	0.026	0.032			
G	1.27	BSC	0.050 BSC				
Н	_	0.50	_	0.020			
K	0.89	1.14	0.035	0.045			
L	0.64	BSC	0.025	BSC			
M	0°	5°	0°	5°			
N	0.76	1.14	0.030	0.045			
Р	11.05	11.30	0.435	0.445			
R	9.15	9.65	0.360	0.380			
S	0.77	1.01	0.030	0.040			

28 LEAD 300 MIL SOJ **CASE 810B-03**



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 DIMENSION A & B DO NOT INCLUDE MOLD PROTRUSION. MOLD PROTRUSION SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

 3. CONTROLLING DIMENSION: INCH.

- S. SONTICLEIN SIMILARY
 A. DIM R TO BE DETERMINED AT DATUM -T-.
 810B-01 AND -02 OBSOLETE, NEW STANDARD 810B-03.

	MILLIM	ETERS	INC	HES		
DIM	MIN	MAX	MIN	MAX		
Α	18.29	18.54	0.720	0.730		
В	7.50	7.74	0.295	0.305		
С	3.26	3.75	0.128	0.148		
D	0.39	0.50	0.015	0.020		
E	2.24	2.48	0.088	0.098		
F	0.67	0.81	0.026	0.032		
G	1.27	BSC	0.050 BSC			
Н	_	0.50	_	0.020		
K	0.89	1.14	0.035	0.045		
L	0.64	BSC	0.025	BSC		
M	0°	10°	0°	10°		
N	0.76	1.14	0.030	0.045		
Р	8.38	8.64	0.330	0.340		
R	6.60	6.86	0.260	0.270		
S	0.77	1.01	0.030	0.040		

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MCM6227B/D